A 16KB Electrically Erasable Nonvolatile Memory

IN 1980, JOHNSON et al. (Intel) described an electrically erasable nonvolatile memory. This device used a Floating Gate Tunnel Oxide (FLOTOX) two transistor cell. The cell size was 0.85 mil\(^2\) using 3.5 µm technology. Tunnel oxide thickness was less than 200 Angstrom, and endurance of more than 10\(^5\) cycles was reported. This cell and the design techniques were widely adopted by the industry on many other memories.